

Highly Dynamic MagnetoResistive Current Sensor (I_{PN} = 50 A)

Preliminary data sheet

The CMS3000 current sensor family is designed for highly dynamic electronic measurement of DC, AC, pulsed and mixed currents with integrated galvanic isolation. The MagnetoResistive technology enables an excellent dynamic response without the hysteresis that is present in iron core based designs.

With a bandwidth of 2 MHz and a temperature range of -40 °C to +105 °C the CMS3000 enables new application fields for highly-dynamic and compact current measurement.

The CMS3000 product family offers PCB-mountable THT current sensors in the range of 5 A up to 100 A nominal current for industrial applications.



CMS3050

Product overview CMS3050

Product description	Package	Delivery Type
CMS3050ABA	THT	Tray

Quick reference guide

Symbol	Parameter	Min.	Тур.	Max.	Unit
V_{CC}	Supply voltage	±12	±15	-	V
I _{PN}	Primary nominal current (RMS)	-	-	50	A
I _{PR}	Primary measuring range 1)	-150	-	+150	А
f_{co}	Upper cut-off frequency (-3 dB)	-	2	-	MHz
ε _Σ	Overall accuracy 2)	-	±1	±1.6	% of I_{PN}

 $^{1)}$ For 3 s in a 60 s interval (RMS \leq $I_{PN})$ and V_{CC} = ±15 V.

 $^{2)}$ $~~\boldsymbol{\epsilon}_{\Sigma}=\boldsymbol{\epsilon}_{G}$ & $\boldsymbol{\epsilon}_{off}$ & $\boldsymbol{\epsilon}_{lin}~~with~V_{CC}=\pm15~V,~I_{P}=I_{PN},~T_{amb}=25~^{\circ}C$

Qualification overview

Standard	Name	Status
2002/95/EC	RoHS-conformity	Approval
EN 61010	CE-sign	Intended
EN 61800-5-1: 2007	Adjustable speed electrical power drive systems	Intended
DIN EN 50178	Electronic equipment for use in power installations	Intended
UL508	Industrial control equipment	Intended

Features

- Based on the Anisotropic MagnetoResistive (AMR) effect
- Measuring range up to 3 times nominal current
- Galvanic isolation between primary and measurement circuit
- Pin-compatible with CMS2000 family
- Bipolar 15 V power supply

Advantages

- Very high bandwidth of 2 MHz
- Highly dynamic step response
- Large temperature range –40 °C to +105 °C
- Excellent accuracy
- Negligible hysteresis
- Compact size

Applications

- Electrical motor control
- DC/DC converter
- IGBT gate driver
- Laser diode driver
- Audio amplifier
- Condition Monitoring
- Switched mode power supplies
- Sensorless BLDC motors





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Absolute maximum ratings

In accordance with the absolute maximum rating system (IEC60134).

Symbol	Parameter	Min.	Max.	Unit
V _{CC}	Positive supply voltage	Tbd.	Tbd.	V
V _{SS}	Negative supply voltage	Tbd.	Tbd.	V
I _{PM}	Maximum primary current 1)	-500	+500	А
T _{amb}	Ambient temperature	-40	+105	°C
T _{stg}	Storage temperature	-40	+125	°C
T _B	Busbar temperature	-40	+125	°C

¹⁾ For 20 ms in a 20 s interval (RMS \leq I_{PN}).

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

CMS3050.DSE.03



Highly Dynamic MagnetoResistive Current Sensor (I_{PN} = 50 A)

Electrical data

 T_{amb} = 25 °C; V_{CC} = ±15 V; unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
V_{CC}	Positive supply voltage		+14.3	+15.0	+15.7	V
V_{EE}	Negative supply voltage		-14.3	-15.0	-15.7	V
I _{PN}	Primary nominal current (RMS)		-	-	50	А
I _{PR}	Measuring range ¹⁾		-150	-	+150	А
V _{outN}	Nominal output voltage (RMS)	$I_P = I_{PN}$, See Fig.1	-	2.5	-	V
R _M	Internal burden resistor for output signal		80	115	150	Ω
R_{P}	Resistance of primary conductor		-	-	0.15	mΩ
lq	Quiescent current	$I_{P} = 0$	-	27	30	mA
I _{CN}	Nominal current consumption	$I_{P} = I_{PN}$	-	50	60	mA
I _{CR}	Measuring range current consumption	$I_P \leq I_{PR}$	-	90	100	mA
I _{CM}	Maximum current consumption	$I_P > I_{PR}$	-	-	130	mA

T_{amb} = 25 °C; V_{CC} = ±12 V; unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
V_{CC}	Positive supply voltage		+11.4	+12.0	+12.6	V
V_{EE}	Negative supply voltage		-11.4	-12.0	-12.6	V
I _{PN}	Primary nominal current (RMS)		-	-	50	А
I _{PR}	Measuring range 1)		-100	-	+100	А
V_{outN}	Nominal output voltage (RMS)	$I_P = I_{PN}$, See Fig.1	-	2.5	-	V
R _M	Internal burden resistor for output signal		80	115	150	Ω
R _P	Resistance of primary conductor		-	-	0.15	mΩ
lq	Quiescent current	$I_P = 0$	-	27	30	mA
I _{CN}	Nominal current consumption	$I_{P} = I_{PN}$	-	50	60	mA
I _{CR}	Measuring range current consumption	$I_P \leq I_{PR}$	-	75	90	mA
I _{CM}	Maximum current consumption	$I_P > I_{PR}$	-	-	100	mA

¹⁾ For 3 s in a 60 s interval (RMS $\leq I_{PN}$).



Highly Dynamic MagnetoResistive Current Sensor (IPN = 50 A)

Accuracy

 T_{amb} = 25 °C; V_{CC} = ±15 V; unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
ε _Σ	Overall accuracy 1)	$I_P \leq I_{PN}$	-	1.0	1.6	% of I_{PN}
ε _G	Gain error	$I_{P} \leq I_{PN}$	-	-	0.7	% of I_{PN}
E off	Offset error	$I_P = 0$	-	-	0.8	% of I_{PN}
٤ _{Lin}	Linearity error	$I_{P} \leq I_{PN}$	-	Tbd.	-	% of I_{PN}
ϵ_{Hys}	Hysteresis ²⁾		-	-	Tbd.	% of I_{PN}
PSRR	Power supply rejection rate		-	-	Tbd.	dB
Ν	Noise level (RMS)		-	2.0	2.5	mV

 $T_{amb} = (-25...+85)^{\circ}C$; $V_{CC} = \pm 15$ V; unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Τ ε _G	Maximum temperature induced gain error		-0.9	0	+0.9	% of I_{PN}
$T\epsilon_{\text{off}}$	Maximum temperature induced offset error		-1.0	0	+1.0	% of I_{PN}
$T\boldsymbol{\epsilon}_{\text{Lin}}$	Maximum temperature induced linearity error		-	Tbd.	Tbd.	% of I_{PN}

 $T_{amb} = (-40...+105)^{\circ}C$; $V_{CC} = \pm 15$ V; unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
$T\epsilon_{G}$	Maximum temperature induced gain error		-1.5	0	+1.5	% of I_{PN}
TE _{off}	Maximum temperature induced offset error		-1.5	0	+1.5	% of I_{PN}
$T\epsilon_{Lin}$	Maximum temperature induced linearity error		-	Tbd.	Tbd.	% of I_{PN}

Notes

 $^{1)}~$ Overall accuracy contains $\epsilon_{G},\,\epsilon_{off}$ and $\epsilon_{Lin}.$

 $^{2)}~$ Residual voltage after 3 \cdot I_{PN} DC.



Highly Dynamic MagnetoResistive Current Sensor (I_{PN} = 50 A)

General data

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
T_{amb}	Ambient temperature 1)		-40	-	+105	°C
T_{stg}	Storage temperature		-40	-	+105	°C
Τ _B	Busbar temperature 1)		-40	-	+125	°C
T_{THT}	Solder temperature	For 7 seconds.	-	-	250	°C
m	Mass		-	6.5	-	g

Dynamic data

 T_{amb} = 25 °C; V_{CC} = ±15 V; unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
t _{reac}	Reaction time ²⁾	10 % I_{PN} to 10 % $I_{\text{out},N}$	-	0.02	0.06	μs
t _{rise}	Rise time ²⁾	10 % $I_{\text{out},N}$ to 90 % $I_{\text{out},N}$	-	0.15	0.40	μs
t _{resp}	Response time ²⁾	90 % I_{PN} to 90 % $I_{\text{out},N}$	-	0.01	0.02	μs
f _{co}	Upper cut-off frequency	-3 dB	-	2	-	MHz

Notes

¹⁾ Operating condition.

 $^{2)}~~I_{P}$ = I_{PN} with di/dt of 90 A/µs. See Fig. 2 and 3.



Highly Dynamic MagnetoResistive Current Sensor (I_{PN} = 50 A)

Qualifications

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Vi	Isolation test voltage (RMS)	50/60 Hz, 60 s	-	3.5	-	kV
V_{imp}	Impulse withstand voltage	1.2/50 μs	-	8	-	kV
d _{cp}	Creepage distance		5	-	-	mm
d _{cl}	Clearance distance		5	-	-	mm



Fig. 1: Characteristic of primary current to output voltage according to supply voltage V_{cc} .



Fig.3: Typical output characteristic of the CMS3050ABA due to a primary current jump from 0 A to I_{PN} with di/dt \approx 90 A/µs compared to a RC-filter configuration (green) with the parameters shown in Fig.6.



Fig. 2: Definition of reaction time (t_{reac}), rise time (t_{rise}) and response time (t_{resp}).



Highly Dynamic MagnetoResistive Current Sensor (I_{PN} = 50 A)

Pinning

Pin	Symbol	Parameter
1	V _{CC}	Positive supply voltage
2	V_{SS}	Negative supply voltage
3	GND	Ground
4	SGND	Signal ground
5	V _{out}	Signal output
6	l _{in}	Primary current input
7	I out	Primary current output



Fig. 4: Pinning of CMS3050.

Dimensions



Fig. 5: Package outline with \pm 0.2 mm tolerance and drilling plan with 0.05 mm tolerance.



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Application circuit



Fig. 6: Typical circuit to improve frequency response using a RC-filter network.

Notes

- ¹⁾ V_{out} is positive, if I_P flows from pin " I_{in} " to pin " I_{out} ".
- $^{2)}$ $\,$ The power supply should always be buffered by 47 μF electrolytic capacitor C1 and C2.
- ³⁾ To improve frequency response a RC-filter is recommended according to the followed parameters:

Туре	Rf1	Cf1	Rf2	Cf2	Cf3
CMS3050ABA	470 Ω	47 nF	180 Ω	2.2 nF	2.2 nF



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PCB Layout







Fig. 8: Recommended current path layout.

Additional notes for the designer

- The minimum clearance to other magnetic devices (for example: relay, current conductors and permanent magnets) depends on the strength of their magnetic field. Homogeneous fields should be below 1 kA/m and magnetic field gradients should be lower than 4 kA/m². A conductor carrying 1 A produces a magnetic field of 20 A/m and a magnetic field gradient of 2.5 kA/m² at a distance of 8 mm.
- The maximum operating temperature is primarily limited by the busbar temperature. Care must be taken to keep the busbar temperature below 125 ℃.
- It is recommended to place multiple sensor arrangements with a clearance (A) of at least 20 mm as shown in Fig. 8. A smaller distance will cause cross-talk to adjacent sensors. The primary current paths in the PCB however may not be routed underneath a sensor. The ideal routing is sown in Fig. 9.

The CMS3000 product family

The CMS3025 is a member of the CMS3000 product family offering PCB-mountable THT current sensors from 5 A up to 100 A nominal current with a typical bandwidth of 2 MHz for various industrial applications.

	CMS3005ABA	CMS3015ABA	CMS3025ABA	CMS3050ABA	CMS3100ABA ¹⁾
	SENSOTEC CMS3005	SENSITEC CMS3015	SENSOTEC CMS3025	SENSOTEC CMS3050	SENSOTEC CMS3100
I _{PN}	5 A	15 A	25 A	50 A	100 A
I _{PR}	15 A	45 A	75 A	150 A	300 A

¹⁾ Coming soon.

- I_{PN:} Nominal primary current (RMS)
- $I_{PR:}$ Measurement range (for 1 s in a 60 s interval)

CMS3050 Highly Dynamic MagnetoResistive Current Sensor (I_{PN} = 50 A)

General information

Product status

The product is under development, gualification is ongoing. Deliverables have a sample status. The datasheet is preliminary. Note: The status of the product may have changed since this data sheet was published. The latest information is available on the internet at www.sensitec.com.

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MagnetoResistive Sensors

Sensitec GmbH Georg-Ohm-Straße 11 35633 Lahnau Germany

Fon +49 (0) 6441 9788-0 Fax +49 (0) 6441 9788-17

E-Mail info@sensitec.com www.sensitec.com

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- Position
- Angle
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